

FIG. 1

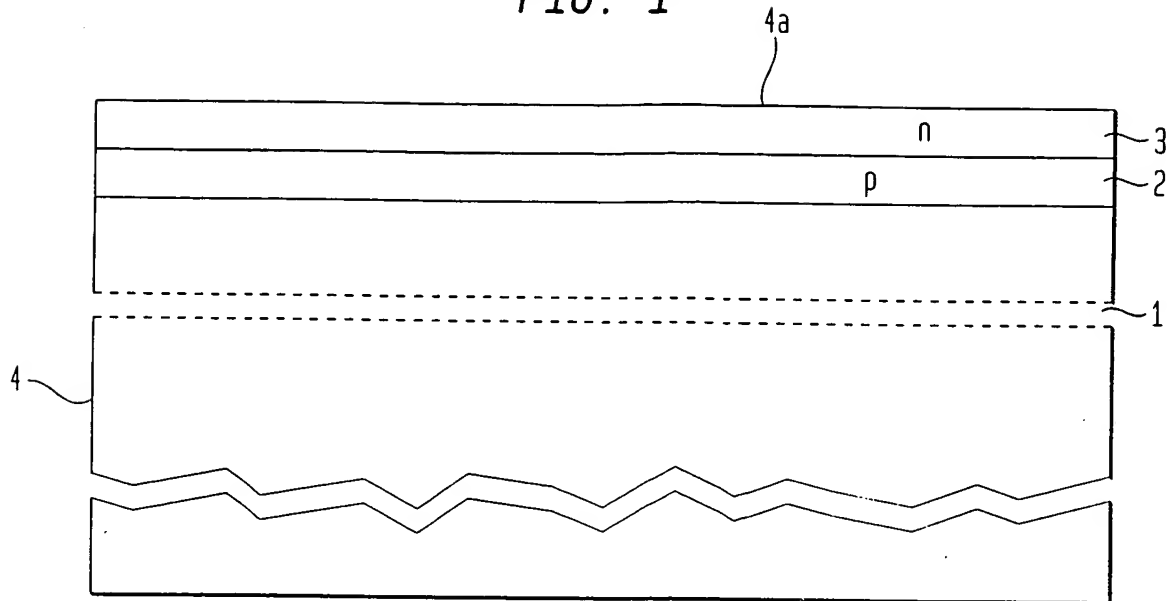


FIG. 2

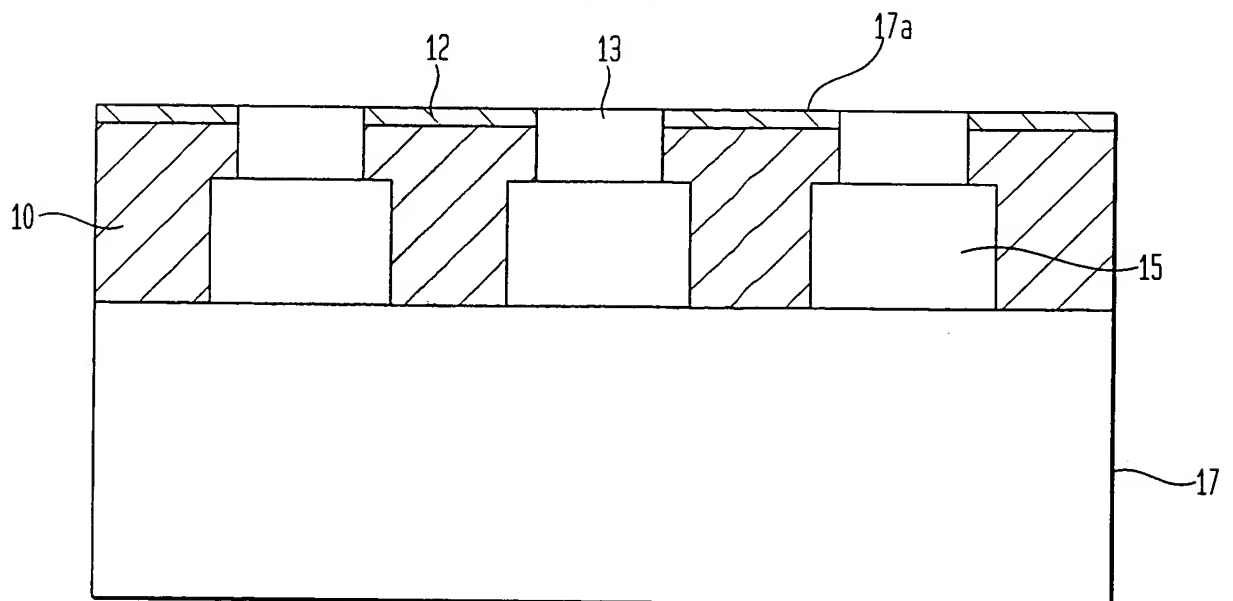


FIG. 3

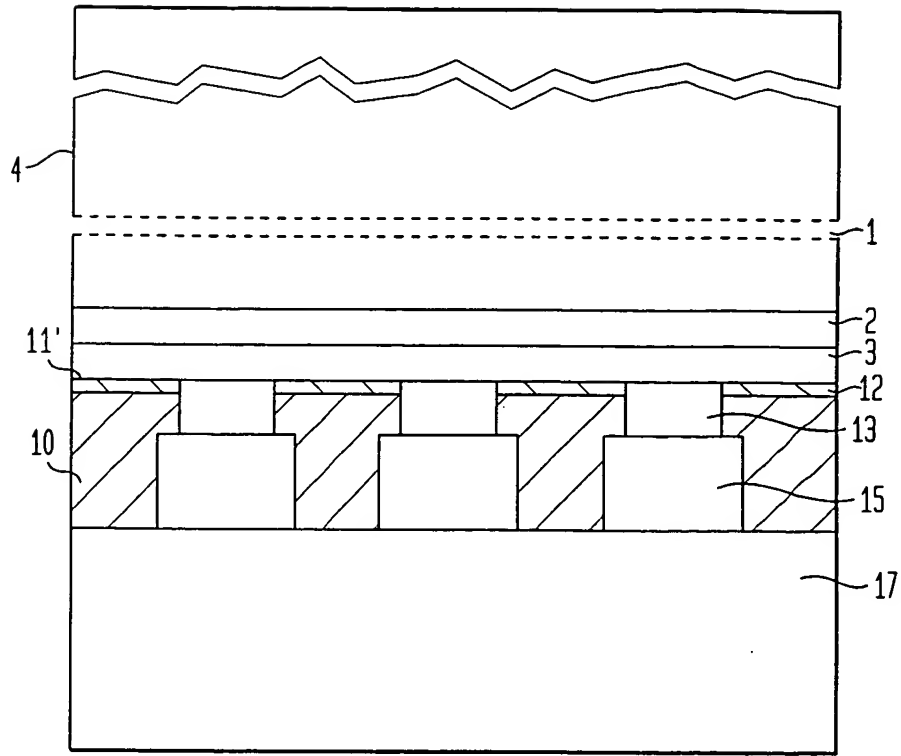
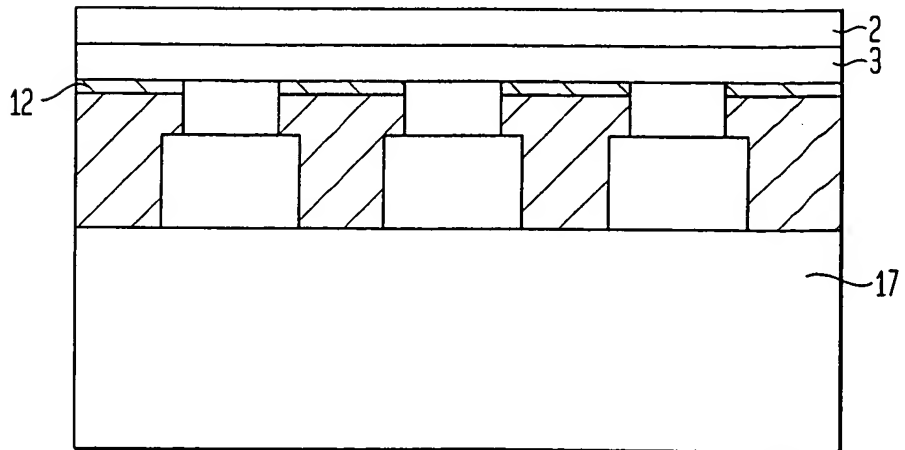


FIG. 4



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A cross-sectional view of a semiconductor device. The structure consists of a substrate 17 at the bottom. Above the substrate is a layer 15. On top of layer 15 are three rectangular blocks 13. Above each block 13 is a thin layer 12. The top surface of the device is a multi-layered structure. It includes a layer 19, a layer 21, and a layer 2'. There are also openings or recesses in the top layer, labeled 2a, 3', and 2a. The right side of the device is labeled 11'.

FIG. 6A

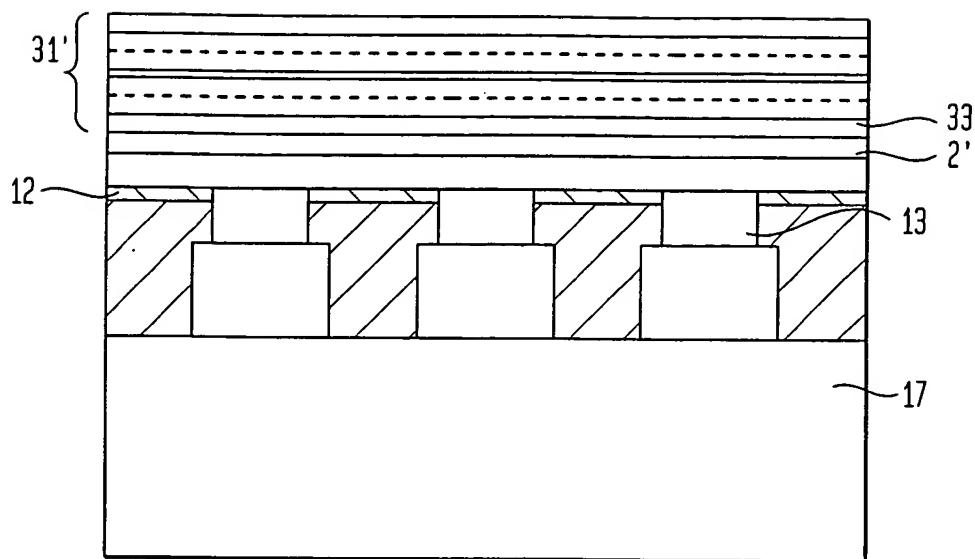
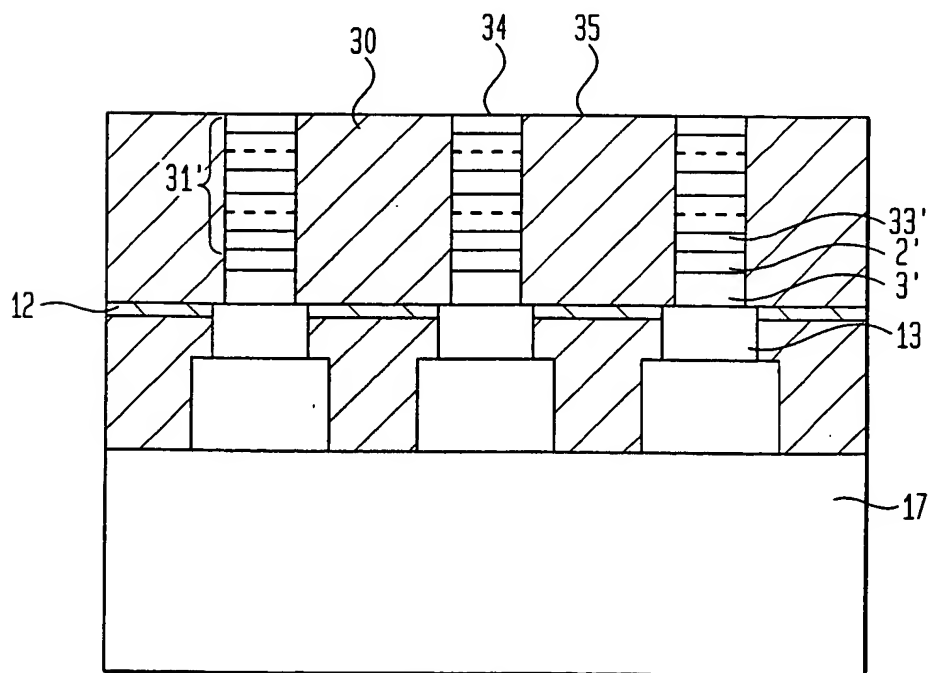
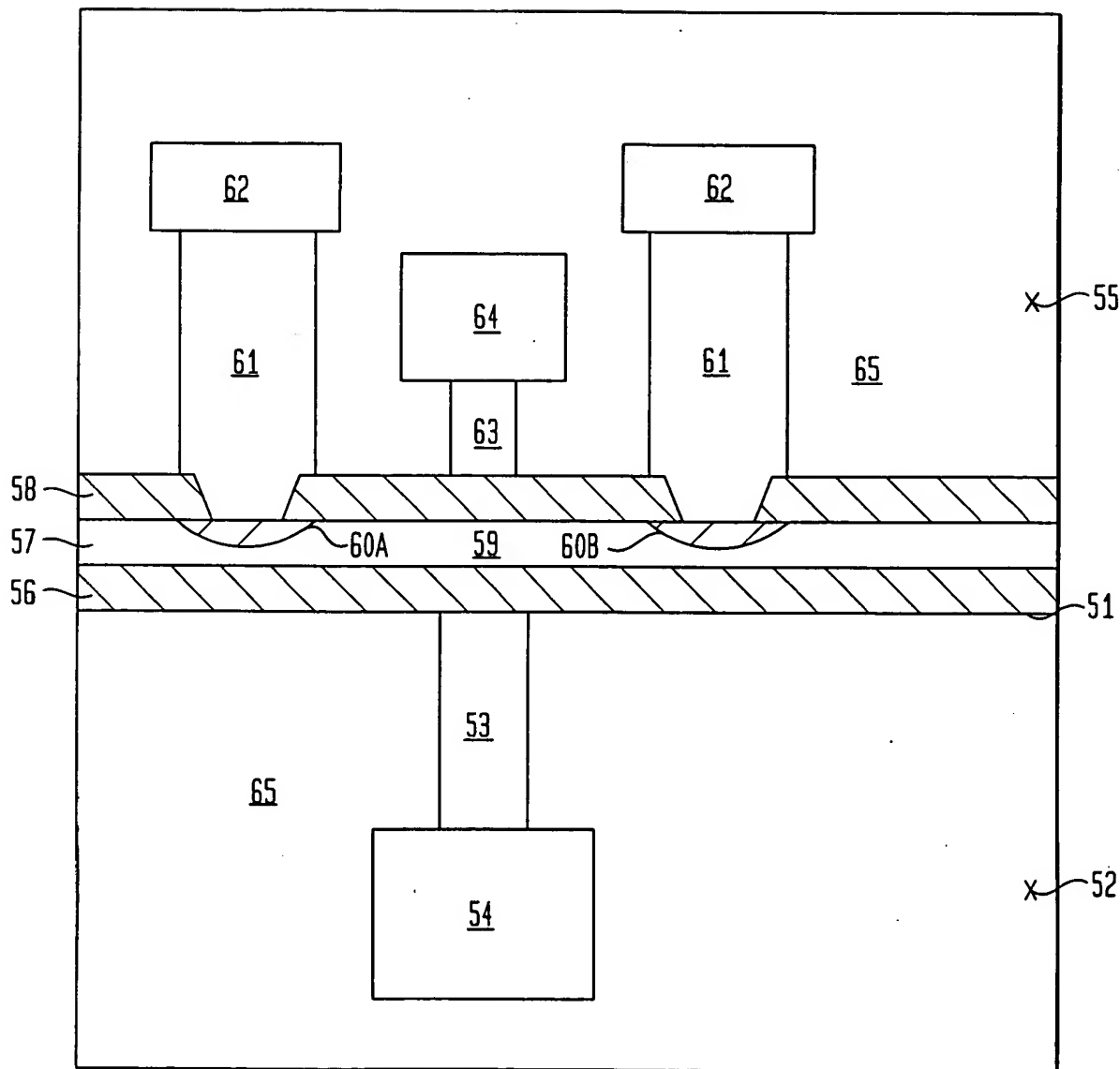


FIG. 6B



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FIG. 7



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